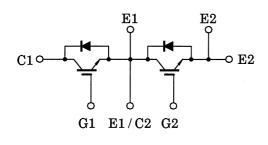
TOSHIBA GTR Module Silicon N Channel IGBT

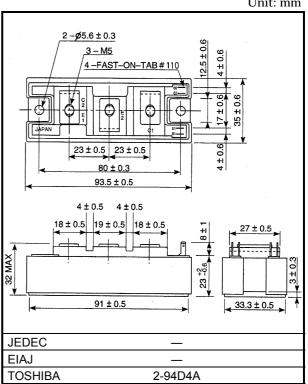
MG50Q2YS50

High Power Switching Applications Motor Control Applications

- High input impedance •
- High speed : $t_f = 0.3 \mu s$ (Max) @Inductive load
- Low saturation voltage •
- : VCE (sat) = 3.6V (Max)
- Enhancement-mode •
- Includes a complete half bridge in one package. .
- The electrodes are isolated from case.

Equivalent Circuit





Weight: 202g

Maximum Ratings (Ta = 25°C)

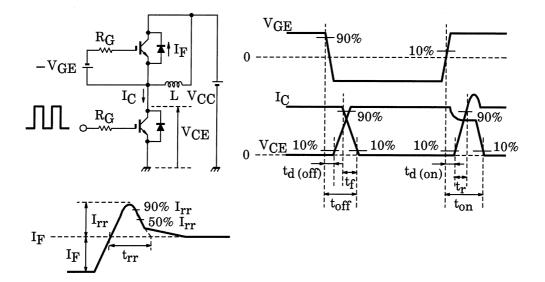
Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	1200	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	I _C (25°C / 80°C)	78 / 50	А	
	1ms	I _{CP} (25°C / 80°C)	156 / 100	~	
Forward current	DC	١ _F	50	А	
	1ms	I _{FM}	100	~	
Collector power dissipation (Tc = 25°C)		Pc	P _C 400		
Junction temperature		Тј	150	°C	
Storage temperature range		T _{stg}	-40 ~ 125	°C	
Isolation voltage		V _{Isol}	2500 (AC 1 minute)	V	
Screw torque (Terminal / mounting)		—	3/3	N∙m	

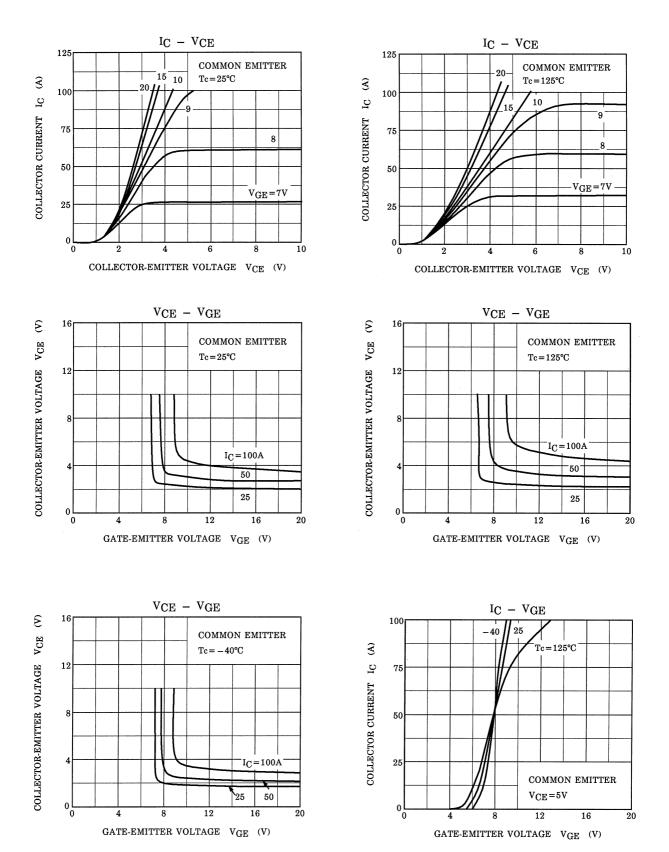
Unit: mm

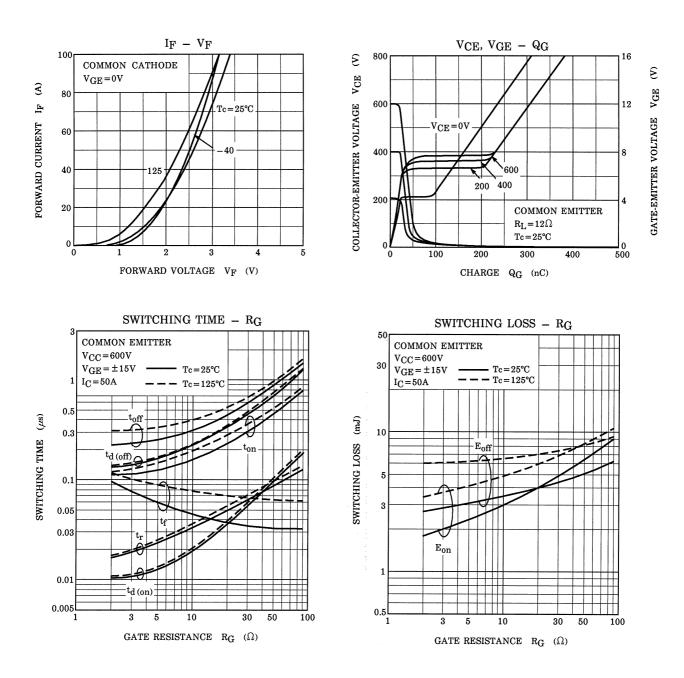
Electrical Characteristics (Ta = 25°C)

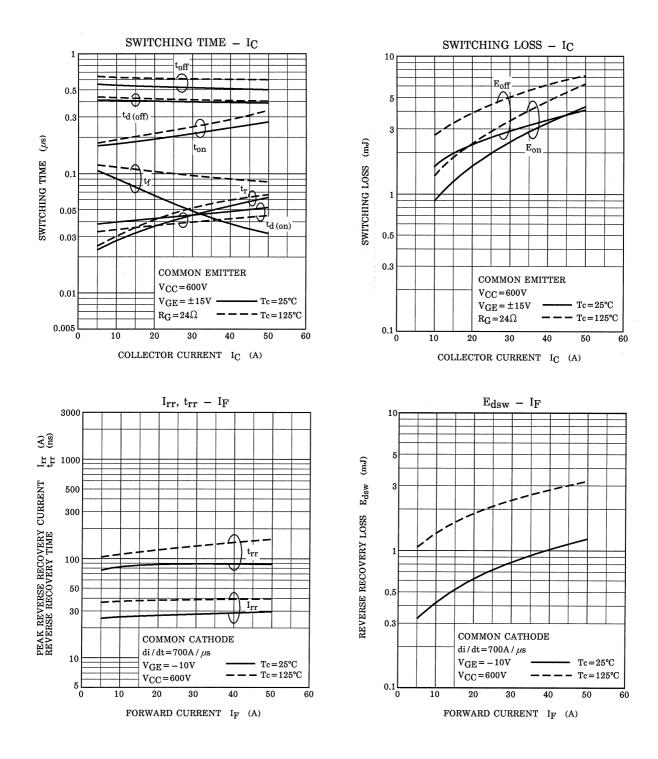
Characteristic		Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	V _{GE} = ±20V, V _{CE} = 0			_	±500	nA
Collector cut-off current		ICES	V _{CE} = 1200V, V _{GE} = 0		_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE (OFF)}	I _C = 50mA, V _{CE} = 5V		3.0	_	6.0	V
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 50A, V _{GE} = 15V	T _j = 25°C	_	2.8	3.6	v
				T _j = 125°C	_	3.1	4.0	
Input capacitance		Cies	V _{CE} = 10V, V _{GE} = 0	/ _{CE} = 10V, V _{GE} = 0, f = 1MHz		6.0	_	nF
Switching time	Turn-on delay time	t _{d (on)}			_	0.05	_	
	Rise time	tr	Inductive load		_	0.05	_	μs
	Turn-on time	t _{on}	$V_{CC} = 600V$ $I_C = 50A$ $V_{GE} = \pm 15V$ $R_G = 24\Omega$		_	0.2	_	
	Turn-off delay time	t _{d (off)}			_	0.5	_	
	Fall time	t _f		(Note 1)	_	0.1	0.3	
	Turn-off time	t _{off}			_	0.6	_	
Forward voltage		VF	I _F = 50 A, V _{GE} = 0		_	2.4	3.5	V
Reverse recovery time		t _{rr}	I _F = 50 A, V _{GE} = -10 V, di / dt = 700 A / μs (Note 1)		_	0.1	0.25	μs
Thermal resistance		R _{th (j-c)}	Transistor stage Diode stage		_	—	0.31	°C / W
					_	_	0.94	

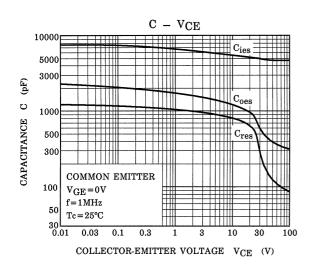
Note 1: Switching time and reverse recovery time test circuit & timing chart

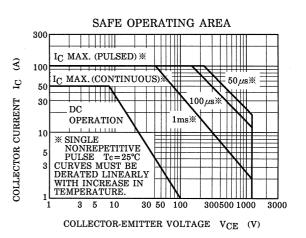


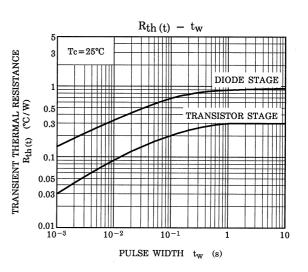


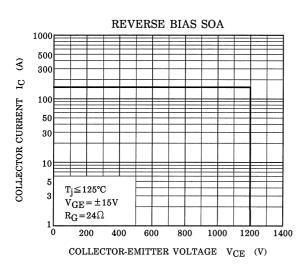


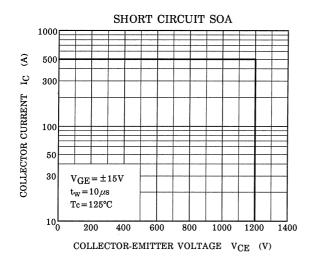












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